

## 最终数据手册

### 英飞凌SiC™ 1200 V SiC 沟道MOSFET

#### 特性

- $T_{vj} = -55 \dots 175^\circ\text{C}$  时  $V_{DSS} = 1200\text{ V}$
- $T_C = 25^\circ\text{C}$  时  $I_{DDC} = 55\text{ A}$
- $R_{DS(on)} = 40\text{ m}\Omega$  ( $V_{GS} = 20\text{ V}$ ,  $T_{vj} = 25^\circ\text{C}$  时)
- 新的性能优化芯片技术 (Gen1p), 改善了  $R_{DS(on)} * A$
- 提高了建议开启电压 ( $V_{GS(on)} = 20\text{ V}$ ) 以降低  $R_{DS(on)}$
- 业界领先的开关能量特性, 可降低开关损耗并减少冷却需求
- 最低的器件电容值, 可实现更高的开关速度和更高的功率密度
- 低  $C_{rss}/C_{iss}$  电容比值和高  $V_{GS(th)}$  的组合, 可避免寄生导通并实现单极性栅极驱动
- 降低了总栅极电荷  $Q_G$ , 可降低驱动功率和损耗
- .XT 芯片粘接技术, 实现业界领先的热性能
- 用于优化开关性能的检测引脚
- 适合高压爬电要求



#### 潜在应用

- 车载充电器
- 直流/直流转换器
- 辅助驱动

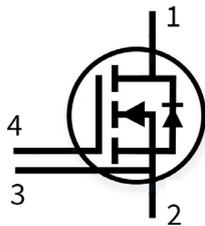
#### 产品验证

- 适合汽车应用。根据 AEC-Q100/101 进行产品验证

#### 描述

引脚定义:

- 1 - 漏极
- 2 - 来源
- 3 - 开尔文检测
- 4 - 栅极



Type	Package	Marking
AIMZHN120R040M1T	PG-TO247-4-STD-NN6.7	A12M1N040

本数据手册的原文使用英文撰写。为方便起见, 英飞凌提供了译文; 由于翻译过程中可能使用了自动化工具, 英飞凌不保证译文的准确性。为确认准确性, 请务必访问 [infineon.com](http://infineon.com) 参考最新的英文版本 (控制文档)。

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1 封装

1 封装

表1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$				260	°C
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.43	0.56	K/W

注： 无需经过生产测试- 经过设计/特性验证。

2 MOSFET

表2 最大额定值

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	$V_{DSS}$	$T_{vj} = -55...175\text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$ , limited by $T_{vj(max)}$	$I_{DCC}$	$V_{GS} = 20\text{ V}$	$T_c = 25\text{ °C}$	55	A
			$T_c = 100\text{ °C}$	39	
Peak drain current, $t_p$ limited by $T_{vj(max)}$	$I_{DM}$	$V_{GS} = 20\text{ V}$	140	A	
Gate-source voltage, max. transient voltage <sup>1)</sup>	$V_{GS}$	$t_p \leq 0.5\ \mu\text{s}, D < 0.01$	-10...25	V	
Gate-source voltage, max. static voltage	$V_{GS}$		-5...23	V	
Avalanche energy, single pulse	$E_{AS}$	$I_D = 15\text{ A}, V_{DD} = 50\text{ V}, L = 2.41\text{ mH}$	269	mJ	
Power dissipation, limited by $T_{vj(max)}$	$P_{tot}$		$T_c = 25\text{ °C}$	268	W
			$T_c = 100\text{ °C}$	134	

1) **重要注释：** 正负栅极源电压的选择会影响器件的长期行为。为了确保器件在计划使用寿命内的正常运行，必须考虑应用说明AN2018-09中描述的设计指南。

表3 建议值

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		20	V
Recommended turn-off gate voltage	$V_{GS(off)}$		0	V

表4 特征值

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 20\text{ A}$	$T_{vj} = 25\text{ °C}$ , $V_{GS(on)} = 20\text{ V}$		40	50	mΩ
			$T_{vj} = 100\text{ °C}$ , $V_{GS(on)} = 20\text{ V}$		56		
			$T_{vj} = 175\text{ °C}$ , $V_{GS(on)} = 20\text{ V}$		80		
			$T_{vj} = 25\text{ °C}$ , $V_{GS(on)} = 18\text{ V}$		44		
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 6.4\text{ mA}$ , $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20\text{ V}$ )	$T_{vj} = 25\text{ °C}$	3.5	4.3	5.1	V
			$T_{vj} = 175\text{ °C}$		3.8		
Zero gate-voltage drain current	$I_{DSS}$	$V_{DS} = 1200\text{ V}$ , $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.3	19	μA
			$T_{vj} = 175\text{ °C}$		50		
Gate leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}$	$V_{GS} = 25\text{ V}$			100	nA
			$V_{GS} = -10\text{ V}$			-100	
Forward transconductance	$g_{fs}$	$I_D = 20\text{ A}$ , $V_{DS} = 20\text{ V}$			12		S
Short-circuit withstand time <sup>1)</sup>	$t_{SC}$	$V_{DD} \leq 800\text{ V}$ , $V_{DS,peak} \leq 1200\text{ V}$ , $T_{vj(start)} = 25\text{ °C}$ , $R_{G,ext} = 2\text{ }\Omega$	$V_{GS(on)} = 20\text{ V}$		1.5		μs
			$V_{GS(on)} = 18\text{ V}$		2		
			$V_{GS(on)} = 15\text{ V}$		2.5		
Internal gate resistance	$R_{G,int}$	$f = 1\text{ MHz}$ , $V_{AC} = 25\text{ mV}$			3.7		Ω
Input capacitance	$C_{iss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$			1264		pF
Output capacitance	$C_{oss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$			63		pF
Reverse transfer capacitance	$C_{rss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$			3.6		pF
$C_{oss}$ stored energy	$E_{oss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$			40		μJ
Total gate charge	$Q_G$	$V_{DD} = 800\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 0/20\text{ V}$ , turn-on pulse			43		nC
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 0/20\text{ V}$ , turn-on pulse			12		nC
Gate-to-drain charge	$Q_{GD}$	$V_{DD} = 800\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 0/20\text{ V}$ , turn-on pulse			7		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 0/20\text{ V}$ , $R_{GS(on)} = 2\text{ }\Omega$ , $R_{GS(off)} = 2\text{ }\Omega$ , $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ °C}$		10		ns
			$T_{vj} = 175\text{ °C}$		10		

(表格续下页.....)

表 4 (续) 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time	$t_r$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	7		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	10		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	20		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	22		
Fall time	$t_f$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	8		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	8		
Turn-on energy	$E_{on}$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	112		$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$	181		
Turn-off energy	$E_{off}$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	56		$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$	64		
Total switching energy	$E_{tot}$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	168		$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$	245		
Virtual junction temperature	$T_{vj}$		-55		175	$^\circ\text{C}$

1)通过设计/特性验证

注: 动态测试电路见图F。

### 3 体二极管 (MOSFET)

表5 最大额定值

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	$V_{DSS}$	$T_{vj} = -55\dots175\text{ }^\circ\text{C}$	1200	V	
Continuous reverse drain current for $R_{th(j-c,max)}$ , limited by $T_{vj(max)}$	$I_{SDC}$	$V_{GS} = 0\text{ V}$	$T_c = 25\text{ }^\circ\text{C}$	45	A
			$T_c = 100\text{ }^\circ\text{C}$	29	
Peak reverse drain current, $t_p$ limited by $T_{vj(max)}$	$I_{SM}$	$V_{GS} = 0\text{ V}$	45	A	

表6 特征值

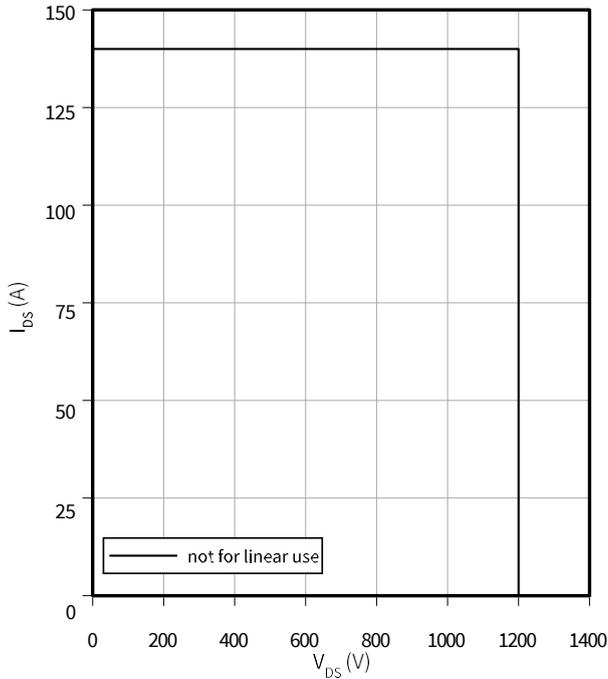
Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source reverse voltage	$V_{SD}$	$I_{SD} = 20 \text{ A}, V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		3.9	5	V
			$T_{vj} = 100 \text{ }^\circ\text{C}$		3.8		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		3.7		
MOSFET forward recovery charge	$Q_{fr}$	$V_{DD} = 800 \text{ V},$ $I_{SD} = 20 \text{ A}, V_{GS} = 0 \text{ V},$ $di_{SD}/dt = 3000 \text{ A}/\mu\text{s}, Q_{fr}$ includes also $Q_C$	$T_{vj} = 25 \text{ }^\circ\text{C}$		135		nC
			$T_{vj} = 175 \text{ }^\circ\text{C}$		350		
MOSFET peak forward recovery current	$I_{frm}$	$V_{DD} = 800 \text{ V},$ $I_{SD} = 20 \text{ A}, V_{GS} = 0 \text{ V},$ $di_{SD}/dt = 3000 \text{ A}/\mu\text{s}, Q_{fr}$ includes also $Q_C$	$T_{vj} = 25 \text{ }^\circ\text{C}$		9		A
			$T_{vj} = 175 \text{ }^\circ\text{C}$		17		
Virtual junction temperature	$T_{vj}$			-55		175	$^\circ\text{C}$

4 特性图

Reverse bias safe operating area (RBSOA)

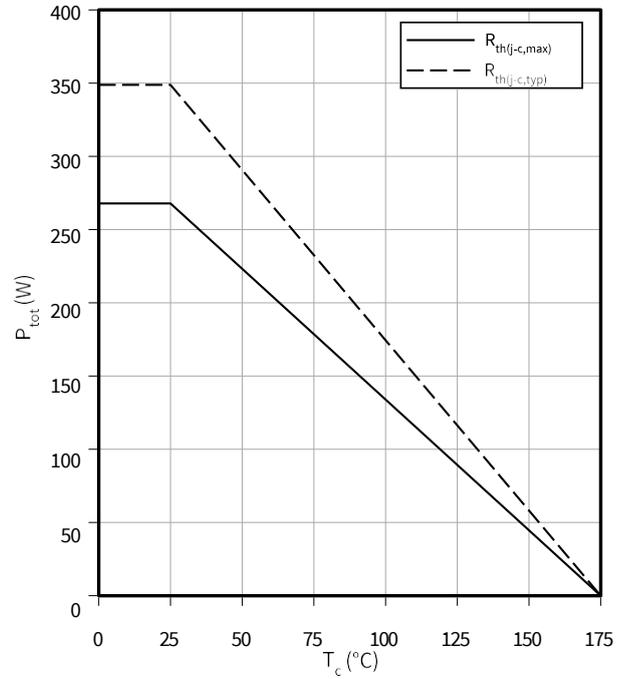
$I_{DS} = f(V_{DS})$

$T_{vj} \leq 175\text{ }^{\circ}\text{C}$ ,  $V_{GS} = 0/20\text{ V}$ ,  $T_c = 25\text{ }^{\circ}\text{C}$



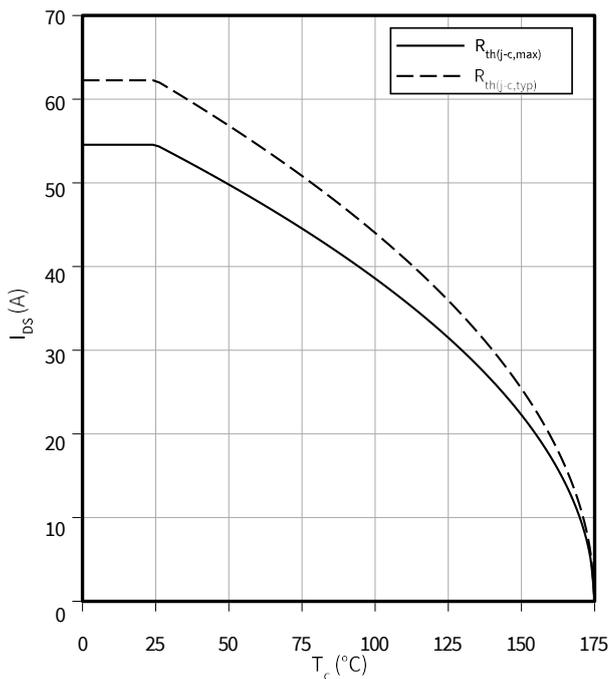
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$



Maximum DC drain to source current as a function of case temperature

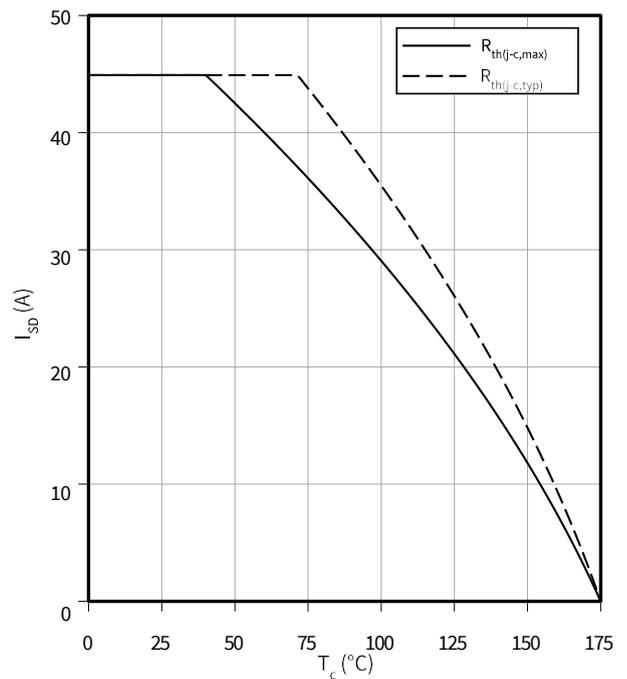
$I_{DS} = f(T_c)$



Maximum source to drain current as a function of case temperature

$I_{SD} = f(T_c)$

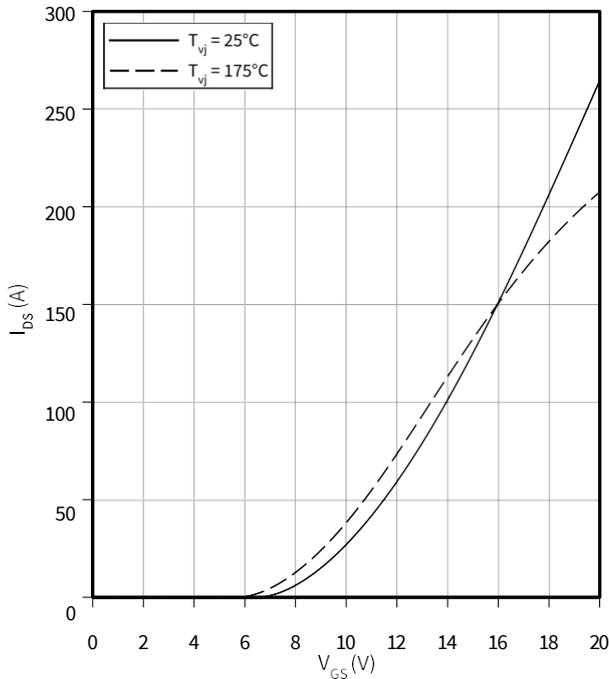
$V_{GS} = 0\text{ V}$



**Typical transfer characteristic**

$I_{DS} = f(V_{GS})$

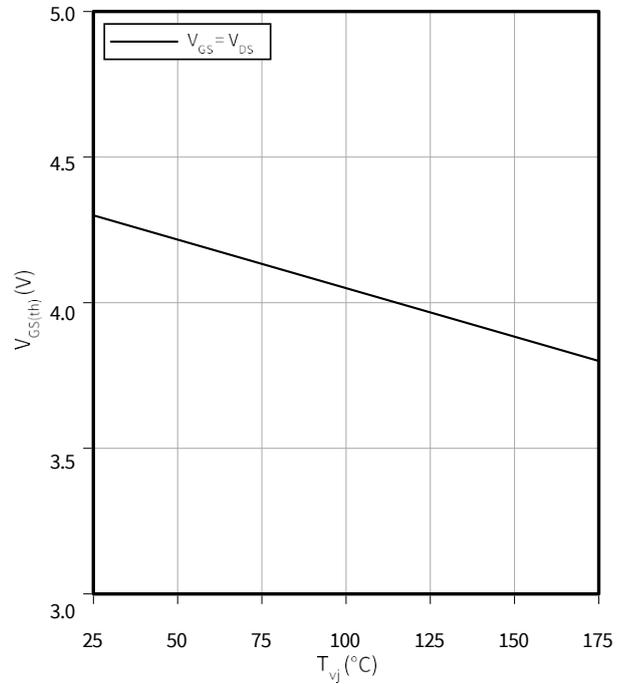
$V_{DS} = 20\text{ V}$



**Typical gate-source threshold voltage as a function of junction temperature**

$V_{GS(th)} = f(T_{vj})$

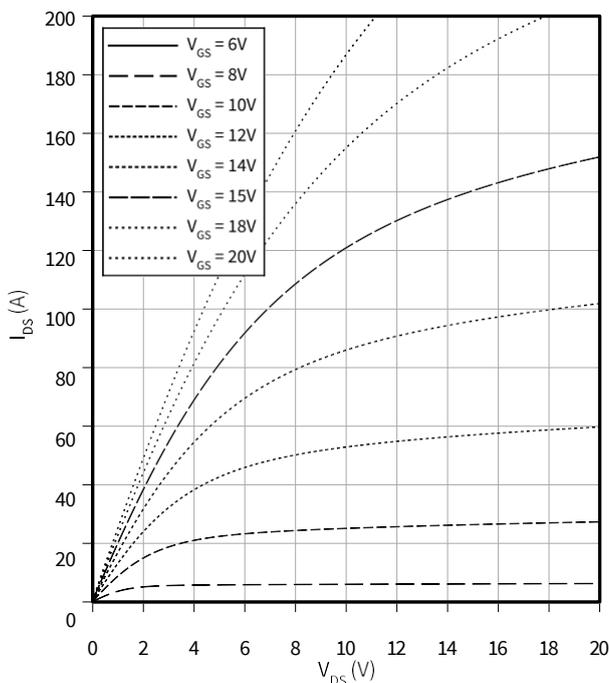
$I_D = 6.4\text{ mA}$



**Typical output characteristic,  $V_{GS}$  as parameter**

$I_{DS} = f(V_{DS})$

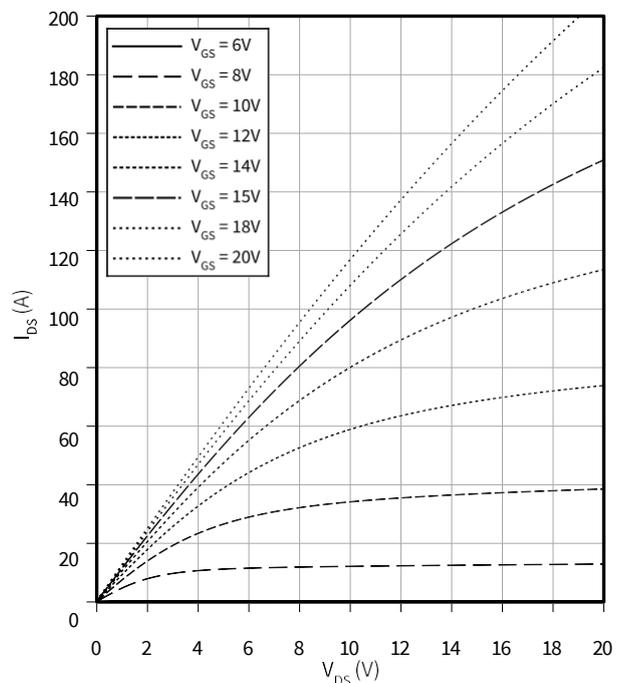
$T_{vj} = 25\text{ °C}$



**Typical output characteristic,  $V_{GS}$  as parameter**

$I_{DS} = f(V_{DS})$

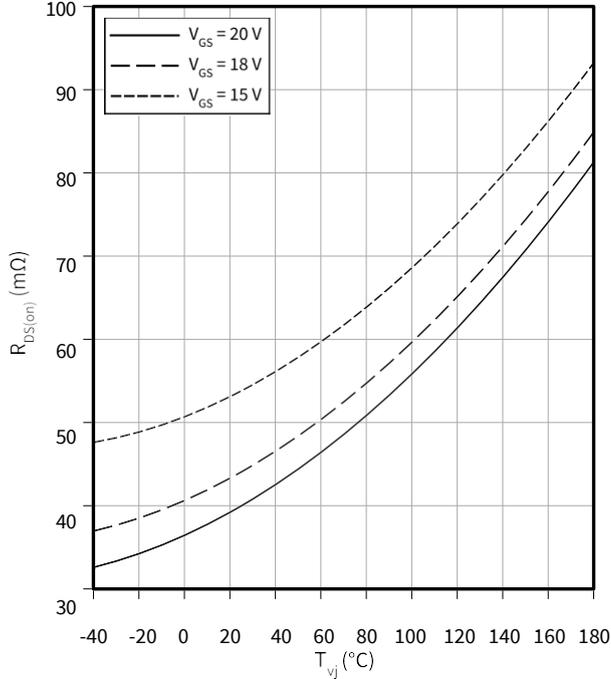
$T_{vj} = 175\text{ °C}$



**Typical on-state resistance as a function of junction temperature**

$$R_{DS(on)} = f(T_{vj})$$

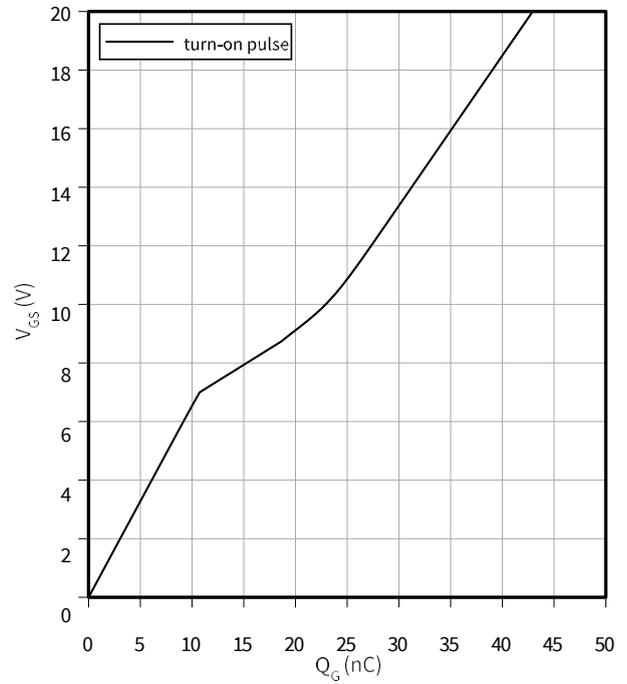
$I_D = 20 \text{ A}$



**Typical gate charge**

$$V_{GS} = f(Q_G)$$

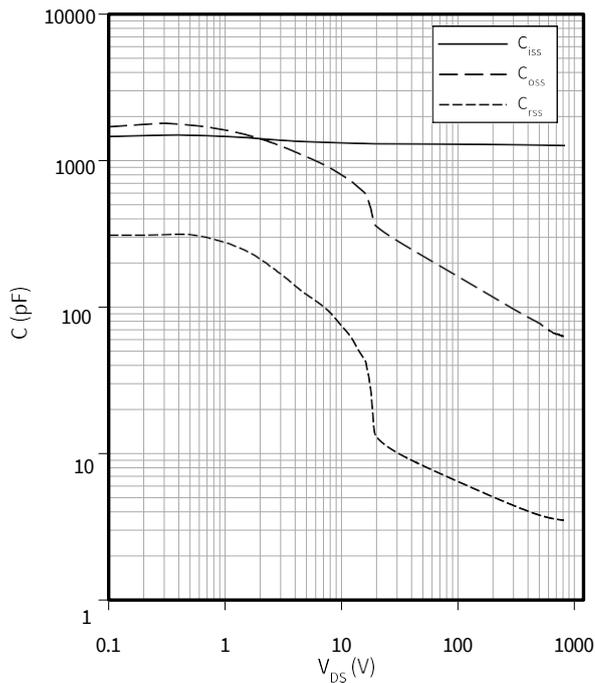
$I_D = 20 \text{ A}, V_{DS} = 800 \text{ V}$



**Typical capacitance as a function of drain-source voltage**

$$C = f(V_{DS})$$

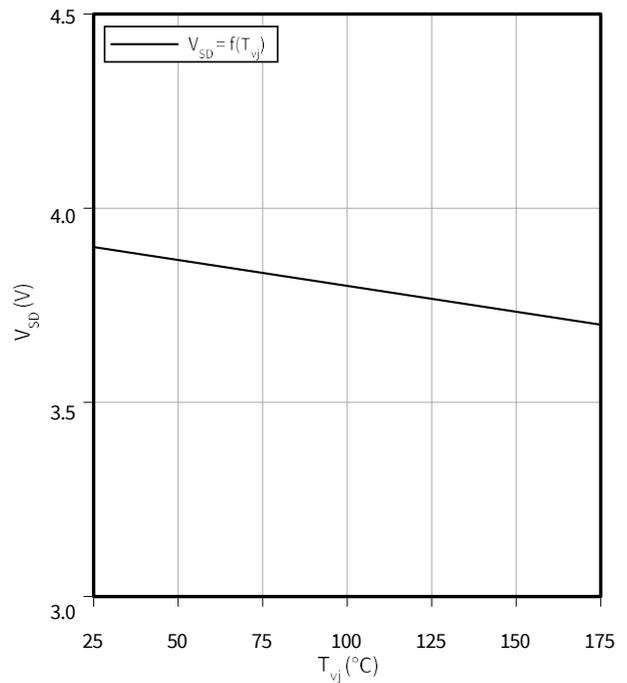
$f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$



**Typical reverse drain voltage as function of junction temperature**

$$V_{SD} = f(T_{vj})$$

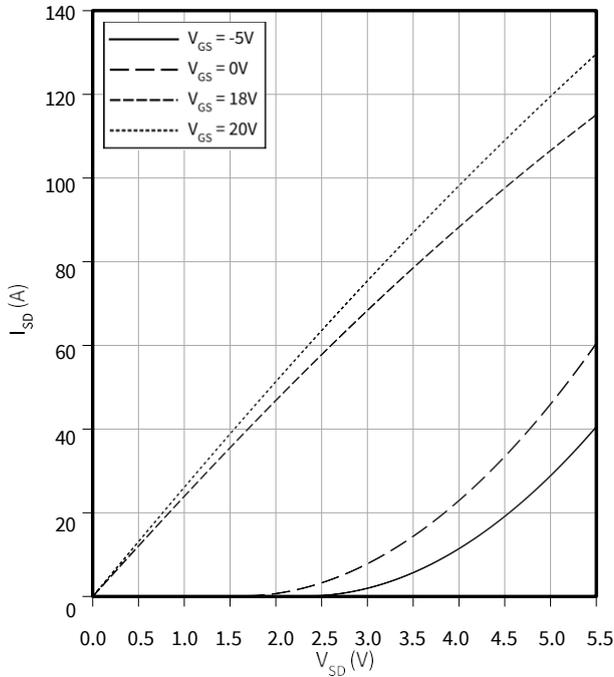
$I_{SD} = 20 \text{ A}, V_{GS} = 0 \text{ V}$



**Typical reverse drain current as function of reverse drain voltage,  $V_{GS}$  as parameter**

$I_{SD} = f(V_{SD})$

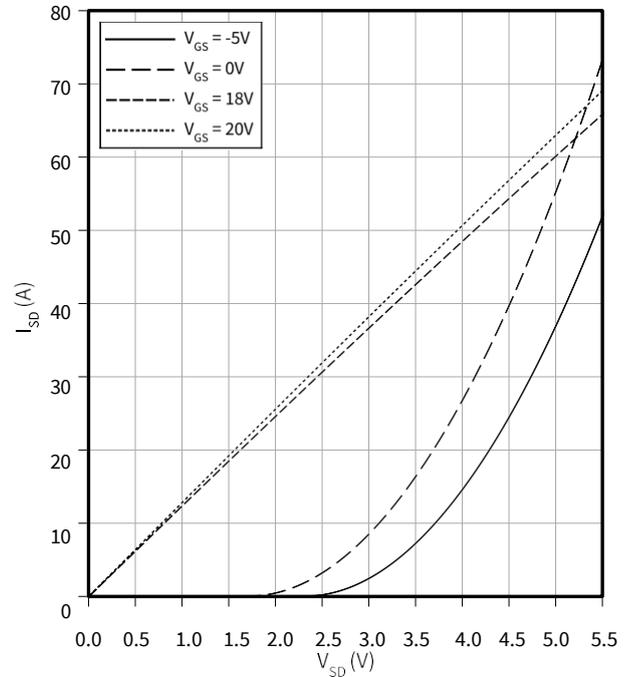
$T_{vj} = 25\text{ °C}$



**Typical reverse drain current as function of reverse drain voltage,  $V_{GS}$  as parameter**

$I_{SD} = f(V_{SD})$

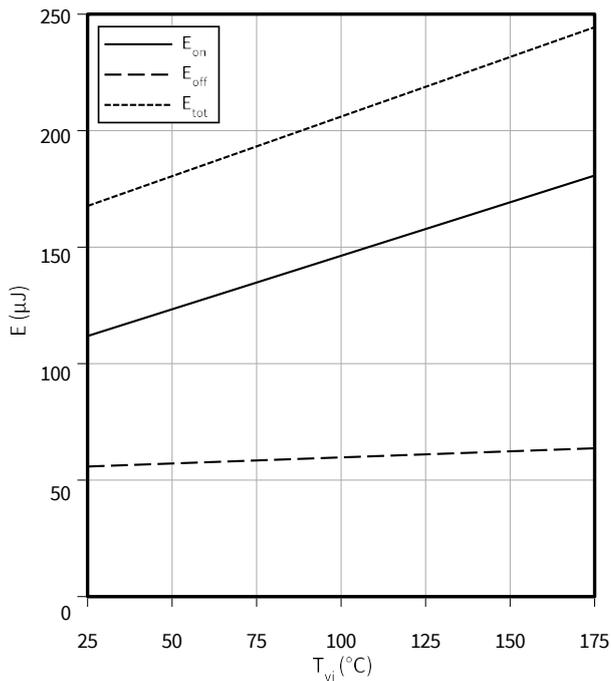
$T_{vj} = 175\text{ °C}$



**Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(T_{vj})$

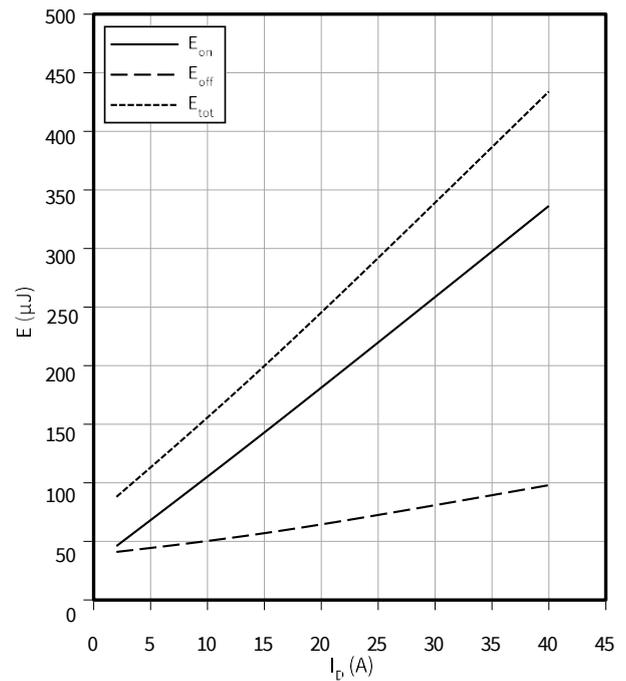
$V_{GS} = 0/20\text{ V}$ ,  $I_D = 20\text{ A}$ ,  $R_{G,ext} = 2\text{ }\Omega$ ,  $V_{DD} = 800\text{ V}$



**Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(I_D)$

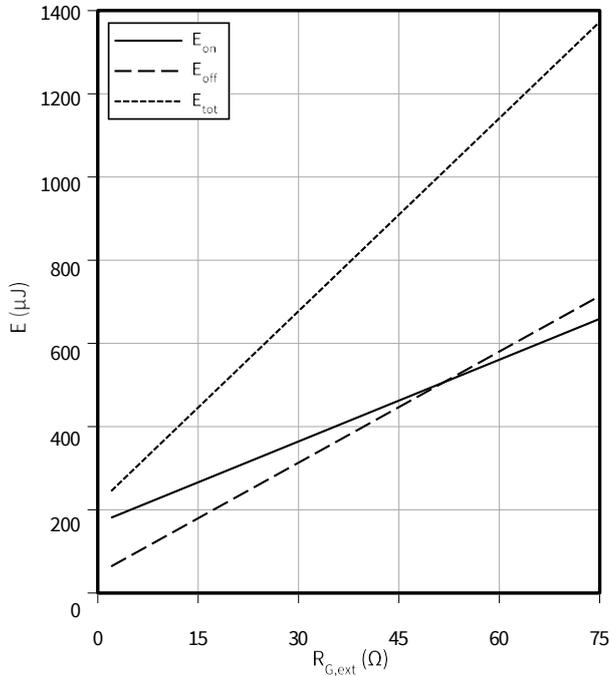
$V_{GS} = 0/20\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $R_{G,ext} = 2\text{ }\Omega$ ,  $V_{DD} = 800\text{ V}$



**Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$$E = f(R_{G,ext})$$

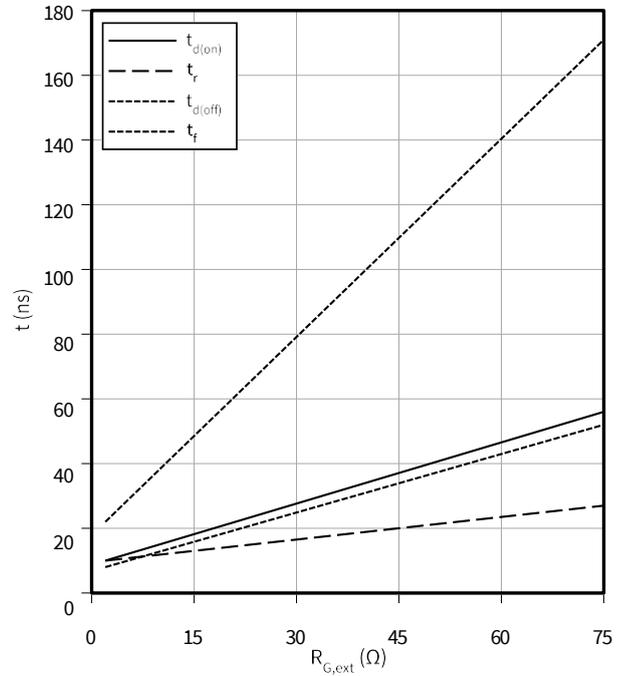
$V_{GS} = 0/20\text{ V}$ ,  $I_D = 20\text{ A}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{DD} = 800\text{ V}$



**Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$$t = f(R_{G,ext})$$

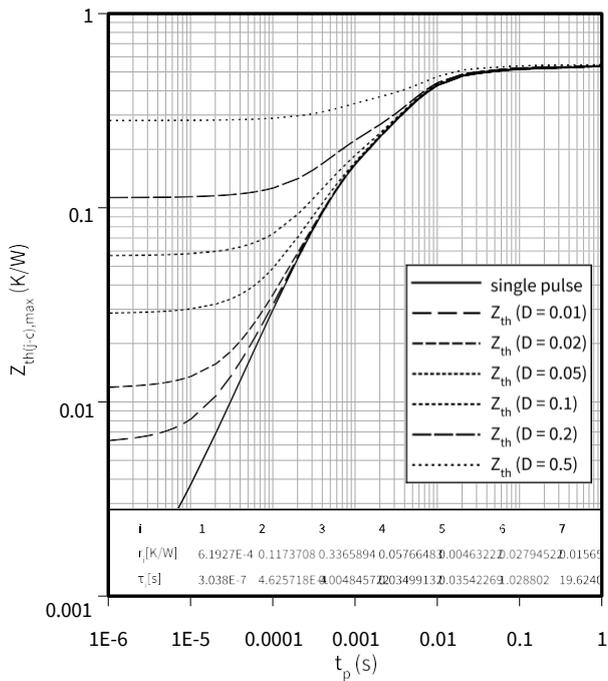
$V_{GS} = 0/20\text{ V}$ ,  $I_D = 20\text{ A}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{DD} = 800\text{ V}$



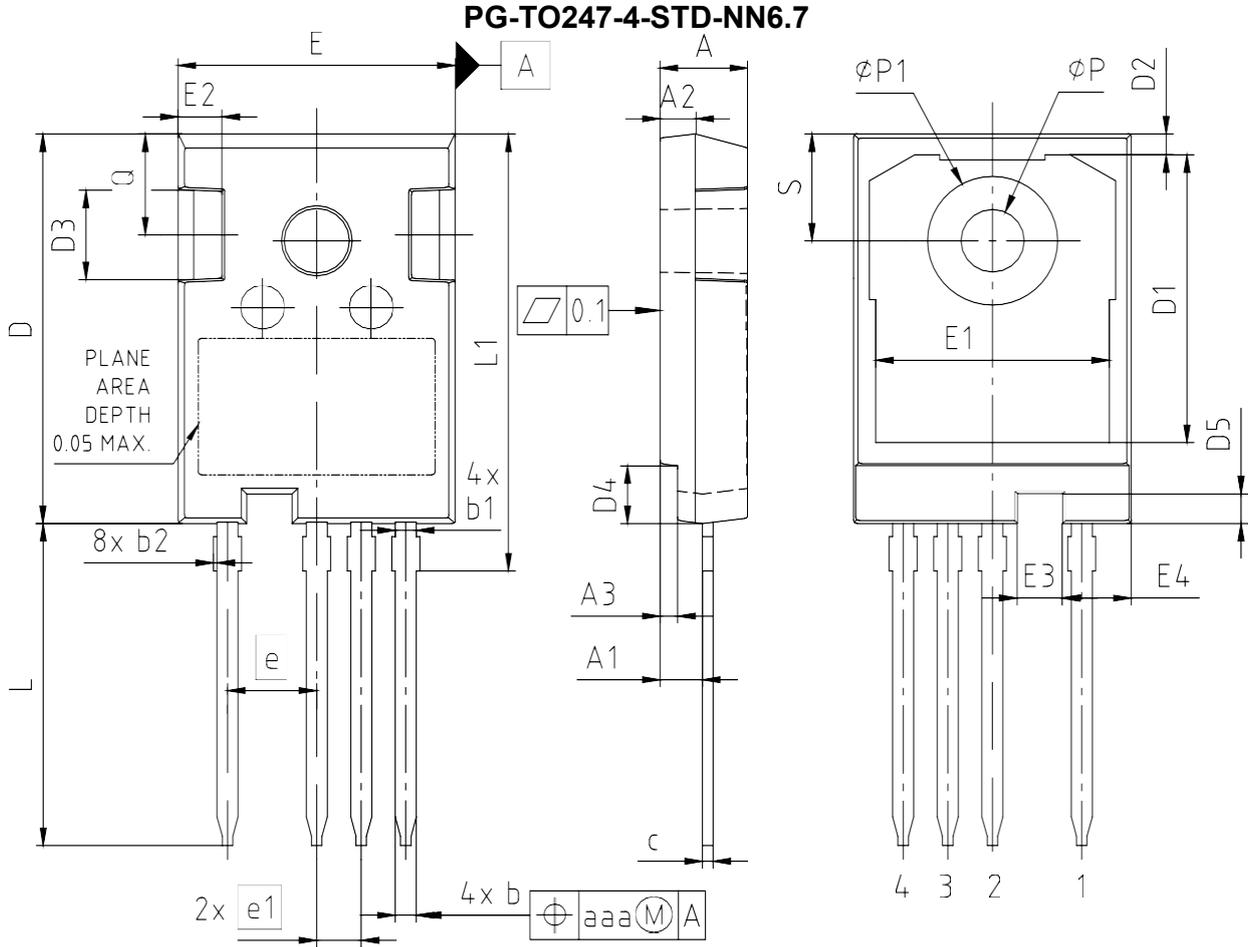
**Max. transient thermal impedance (MOSFET/diode)**

$$Z_{th(j-c),max} = f(t_p)$$

$$D = t_p/T$$



5 封装外形



PACKAGE - GROUP NUMBER: **PG-TO247-4-U05**

DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
<b>A</b>	4.90	5.10	<b>E</b>	15.70	15.90
<b>A1</b>	2.31	2.51	<b>E1</b>	13.10	13.50
<b>A2</b>	1.90	2.10	<b>E2</b>	2.40	2.60
<b>A3</b>	0.90	1.10	<b>E3</b>	2.48	2.68
<b>b</b>	1.16	1.29	<b>E4</b>	3.82	4.02
<b>b1</b>	1.16	1.29	<b>e</b>	5.08	
<b>b2</b>		0.20	<b>e1</b>	2.54	
<b>c</b>	0.59	0.66	<b>N</b>	4	
<b>D</b>	22.30	22.50	<b>L</b>	18.40	18.70
<b>D1</b>	16.25	16.85	<b>L1</b>	24.97	25.27
<b>D2</b>	1.05	1.35	<b>øP</b>	3.50	3.70
<b>D3</b>	5.00	5.20	<b>øP1</b>		7.40
<b>D4</b>	3.22	3.42	<b>Q</b>	5.60	6.00
<b>D5</b>	1.60	1.80	<b>S</b>	6.00	6.30
			<b>aaa</b>	0.25	

NOTE: DIMENSIONS DO NOT INCLUDE MOLDFLASH; PROTRUSION OR GARE BURRS

6 测试条件

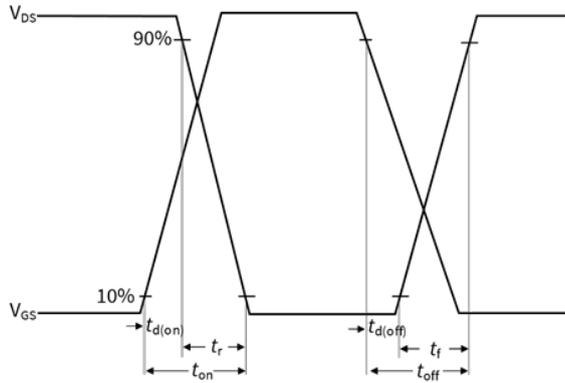


Figure A. Definition of switching times

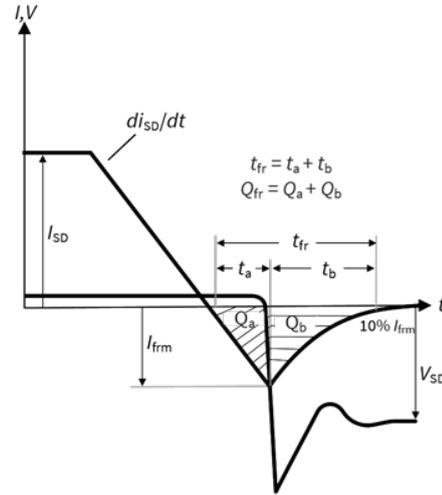


Figure B. Definition of body diode switching characteristics

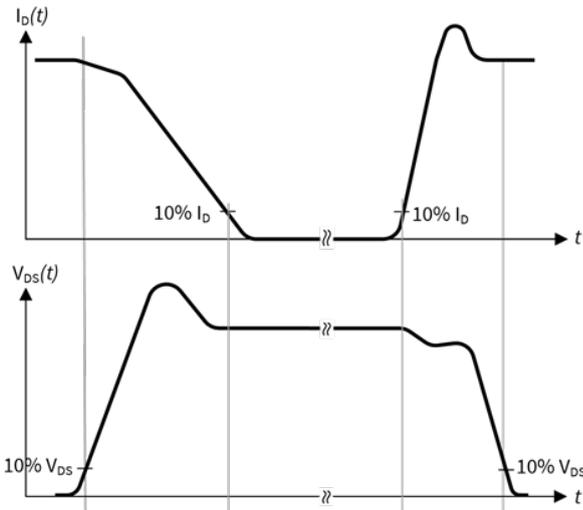


Figure C. Definition of switching losses

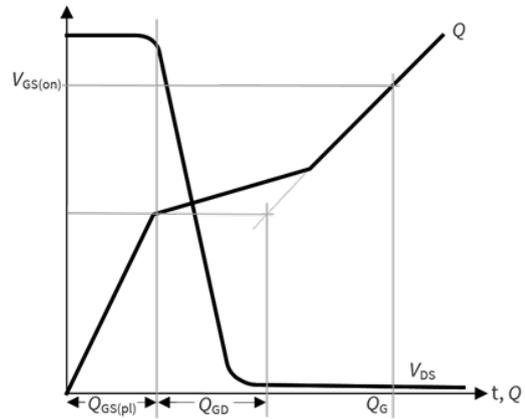


Figure D. Definition of QGD

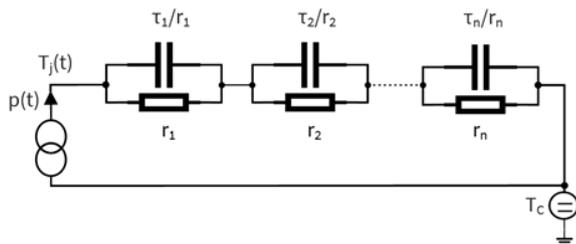


Figure E. Thermal equivalent circuit

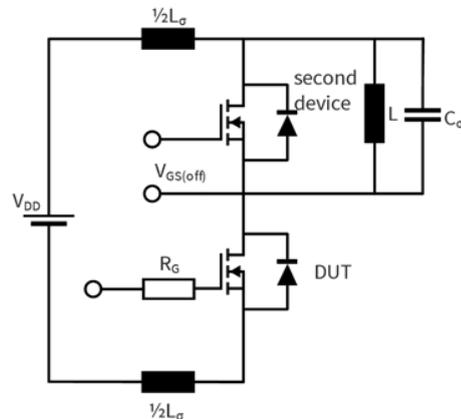


Figure F. Dynamic test circuit  
Parasitic inductance  $L_{\sigma}$ ,  
Parasitic capacitor  $C_{\sigma}$ ,

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修订记录

## 修订记录

Document revision	Date of release	Description of changes
0.10	2022-04-19	Target datasheet
0.20	2023-08-03	Preliminary datasheet
1.00	2023-11-30	Final datasheet



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